



Article Weak Antilocalization Tailor-Made by System Topography in Large Scale Bismuth Antidot Arrays

Michal Krupinski *, Arkadiusz Zarzycki, Yevhen Zabila and Marta Marszałek

Supplementary Material



Figure S1. XRD pattern of the Bi (50 nm) thin film deposited on the flat Si/SiO₂ (100 nm) substrate.

Magnetotransport measurements for Bi arrays with antidot size of 45 nm and 110 nm.



Figure S2. (*a*,*b*) Longitudinal magnetoresistance (MR) and (c) Hall transverse magnetoresistance vs field curves for Bi antidot arrays with antidot size of 45 nm. For clarity, the results of Hall measurements for temperature range 4 K - 20 K were omitted since they are similar to those obtained at 2 K and 50 K.



Figure S3. (**a**,**b**) Longitudinal magnetoresistance (MR) and (**c**) Hall transverse magnetoresistance vs field curves for Bi antidot arrays with antidot size of 110 nm. For clarity, the results of Hall measurements for temperature range 4 K–20 K were omitted since they are similar to those obtained at 2 K and 50 K.



© 2020 by the authors. Submitted for possible open access publication under the terms and conditions of the Creative Commons Attribution (CC BY) license (http://creativecommons.org/licenses/by/4.0/).